

And I hereby appoint Adam C. Volentine, Reg. No. 33289 and William S. Francos, Reg. No. 38,456, and the firm of *VOLENTINE FRANCOS, P.L.L.C.*, jointly and severally, attorneys to prosecute this application and to transact all business in the U.S. Patent and Trademark Office connected therewith.

I hereby authorize the U.S. attorneys named herein to accept and following instructions from Samsung Electronics Co., Ltd. as to any action to be taken in the U.S. Patent and Trademark Office regarding this application without direct communication between the U.S. attorneys and myself. In the event of a change in the persons from whom instructions may be taken, the U.S. attorneys named herein will be so notified by me.

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REISSUE ERROR

I hereby declare as follows:

(1) This is a reissue application of U.S. Patent No. 6,255,181 B1 (hereinbelow the '181 patent), issued July 3, 2001.

(2) I believe the '181 patent to be wholly or partly inoperative by reason of the patentee claiming less than the patentee had a right to claim.

(3) The original application (Serial No. 09/161,979, filed September 29, 1998) of the '181 patent included a single claim ("claim 9") directed to the third embodiment of the invention, which is shown in FIGS. 3A-3F of the '181 patent.

(4) In an Office Action dated October 6, 1999, claim 9 of the original application was rejected under 35 U.S.C. §102(b) as being unpatentable over Fulford, Jr. et al. (U.S. Patent No. 5,923,983).

(5) In an Amendment dated December 9, 1999, claim 9 of the original application was canceled without prejudice.

(6) The cancellation of claim 9 of the original application was in error. Instead, claim 9 should have been amended to clarify that the "buffering layer" (35 of FIG. 3B) is "deposited over" the semiconductor substrate (31) having the gate pattern (32, 33) and lightly doped regions (34). Also, in addition to amending claim 9, dependent claims should have been added to define the buffering layer as either SiO₂ or SiN, to define the thickness of the buffering layer as about 30Å or more, and to define the transition metal as Co, Ti and/or Ni. Such an amended claim 9 and new dependent claims would have overcome the rejection under 35 U.S.C. §102(b) since Fulford, Jr. et al. relies on oxidation of underlying silicon-containing layers to form a polycrystalline oxide 24, since Fulford, Jr. et al. does not quantify the thickness of the polycrystalline oxide 24, and since Fulford, Jr. et al. does not specify the materials for formation of a silicide. Also, it is believed that the last two steps of claim 9 are not necessary to define over the prior art, and accordingly, to adequately claim the third embodiment of the invention, an additional set of claims should have been added which do not require the formation of a transition metal and subsequent anneal.

(7) To correct the error described in paragraph (6), the amendment submitted herewith adds new claims 9-17. New independent claim 9 is the same as the claim 9 of the original application, except that the phrase "forming a buffering layer on" has been changed to -- depositing a buffering layer over --. New dependent claim 10 recites the buffering layer as being SiO₂, new dependent claim 11 recites the buffering layer as being SiN, new dependent claim 12 recites the thickness of the buffering layer as about 30Å or more, and new dependent claim 13 recites the transition metal as Co, Ti and/or Ni. New independent claim 14 is the same as new independent claim 9, except that the last two steps of claim 9 do not appear in claim 14. New dependent claim 15 recites the buffering layer as being SiO₂, new dependent claim 16 recites the buffering layer as being SiN, and new dependent claim 17 recites the thickness of the buffering layer as about 30Å or more.

(8) Support for depositing a SiO₂ or SiN buffering layer at a thickness of about 30Å or more over the substrate (as recited in new claims 9-12 and 14-16) and can be found at least at column 5, lines 16-23, of the '181 patent. Support for a transition metal of Co, Ti and/or Ni (as recited in new claims 13 and 17) can be found at least at column 5, lines 46-48, of the '181 patent. No new matter has been added.

(9) All errors described herein and being corrected by this reissue application occurred without deceptive intention.

I further declare that all statements made herein of my own knowledge are true, and that all statements on information and believe are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code, and that such willful false statements may jeopardize the validity of the application or any patent issuing thereon.

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